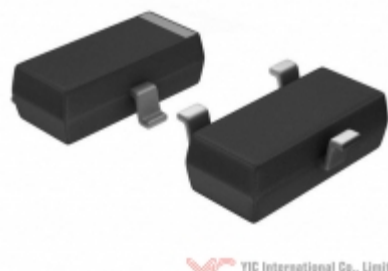








	<h2 style="color: red;">FJV3114RMTF</h2>	
	<b>Hersteller-Teilenummer:</b>	FJV3114RMTF
	<b>Hersteller / Marke:</b>	AMI Semiconductor / ON Semiconductor
	<b>Teil der Beschreibung:</b>	TRANS PREBIAS NPN 200MW SOT23-3
Image may be representation. See specs for product details.	<b>Datenblätter:</b>	<a href="#">1.FJV3114RMTF.pdf</a> <a href="#">2.FJV3114RMTF.pdf</a>
	<b>RoHs Status:</b>	Bleifrei / RoHS-konform
	<b>Lagerzustand:</b>	New original, 26500 pcs Stock Available.
	<b>Liefern von:</b>	Hong Kong
	<b>Versandweg:</b>	DHL/Fedex/TNT/UPS/EMS

### Spezifikationen

Teilenummer	FJV3114RMTF
Hersteller	AMI Semiconductor / ON Semiconductor
Beschreibung	TRANS PREBIAS NPN 200MW SOT23-3
Kategorie	<a href="#">Diskrete Halbleiterprodukte</a> > <a href="#">Transistoren-Bipolar</a>
Teilstatus	26500 pcs Stock
Hersteller Standard Vorlaufzeit	13 Weeks
detaillierte Beschreibung	Pre-Biased Bipolar Transistor (BJT) NPN - Pre-Biased
Serie	-
Befestigungsart	Surface Mount
Leistung - max	200mW
Verpackung / Gehäuse	TO-236-3, SC-59, SOT-23-3
Supplier Device-Gehäuse	SOT-23-3 (TO-236)
Transistor-Typ	NPN - Pre-Biased
Strom - Kollektor (Ic) (max)	100mA
Spannung - Kollektor-Emitter-Durchbruch (max)	50V
VCE Sättigung (Max) @ Ib, Ic	300mV @ 500µA, 10mA
Strom - Collector Cutoff (Max)	100nA (ICBO)
DC Stromgewinn (HFE) (Min) @ Ic, VCE	68 @ 5mA, 5V
Frequenz - Übergang	250MHz
Verpackung	Original-Reel®
Basisteilenummer	FJV3114
Widerstand - Basis (R1)	4.7 kOhms
Widerstand - Emitterbasis (R2)	47 kOhms
Bleifreier Status / RoHS-Status	Lead free / RoHS Compliant
Feuchtigkeitsempfindlichkeitsniveau (MSL)	1 (Unlimited)
Andere Namen	FJV3114RMTFDKR

FJV3114RMTF ist neu im Original, Suche FJV3114RMTF Datenblätter, PDF, Inventar bei Y-IC.com Online, Bestellen Sie FJV3114RMTF AMI Semiconductor / ON Semiconductor mit Garantie und Vertrauen. Anfrage FJV3114RMTF: [Info@Y-IC.com](mailto:Info@Y-IC.com)

Sie können auch interessiert sein:

 <b>FJV3112RMTF</b> Fairchild/ON Semiconductor TRANS PREBIAS NPN 200MW SOT23-3	 <b>FJV3114RMTF</b> Fairchild/ON Semiconductor TRANS PREBIAS NPN 200MW SOT23-3	 <b>FJV3112RMTF</b> AMI Semiconductor / ON Semiconductor TRANS PREBIAS NPN 200MW SOT23-3	 <b>FJV3115RMTF</b> Fairchild/ON Semiconductor TRANS PREBIAS NPN 200MW SOT23-3
 <b>FJV4101RMTF</b> AMI Semiconductor / ON Semiconductor TRANS PREBIAS PNP 200MW SOT23-3	 <b>FJV3115RMTF</b> AMI Semiconductor / ON Semiconductor TRANS PREBIAS NPN 200MW SOT23-3	 <b>FJV3111RMTF</b> Fairchild/ON Semiconductor TRANS PREBIAS NPN 200MW SOT23-3	 <b>FJV3113RMTF</b> AMI Semiconductor / ON Semiconductor TRANS PREBIAS NPN 200MW SOT23-3

heiße Teile

Mehr

⊕ FJV3102RMTF	➔ FJV3102RMTF	➔ FJV3103RMTF	D FJV3103RMTF	➔ FJV3104RMTF
⊕ FJV3104RMTF	⊕ FJV3105RMTF	D FJV3105RMTF	➔ FJV3106RMTF	➔ FJV3106RMTF
⊕ FJV3107RMTF	⊕ FJV3107RMTF	⊕ FJV3108RMTF	➔ FJV3108RMTF	➔ FJV3109R
D FJV3109RMTF	⊕ FJV3109RMTF	⊕ FJV3110RMTF	⊕ FJV3110RMTF	➔ FJV3111RMTF
➔ FJV3111RMTF	➔ FJV3112RMTF	⊕ FJV3112RMTF	⊕ FJV3113RMTF	➔ FJV3113RMTF
➔ FJV3114RMTF	➔ FJV3115RMTF	D FJV3115RMTF	⊕ FJV4101RMTF	⊕ FJV4101RMTF
⊕ FJV4102RLIMTF	D FJV4102RMTF	➔ FJV4102RMTF	➔ FJV4103RMTF	➔ FJV4103RMTF
⊕ FJV4104RMTF	⊕ FJV4104RMTF	➔ FJV4105RMTF	➔ FJV4105RMTF	➔ FJV4106RMTF
⊕ FJV4106RMTF	⊕ FJV4107RMTF	⊕ FJV4107RMTF	D FJV4108RMTF	➔ FJV4108RMTF
➔ FJV4109RMTF	⊕ FJV4109RMTF	⊕ FJV4110RMTF	⊕ FJV4110RMTF	➔ FJV4111RMTF

Contact us: [Info@Y-IC.com](mailto:Info@Y-IC.com)

HINZUFÜGEN: Einheit A5-B5 Nr.509, 5 / F Sing Win Fabrikgebäude, 15-17 Shing Yip St, Kwun Tong, Kowloon, HongKong.

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